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- (54) **Title:** APPARATUSES, SENSE CIRCUITS, AND METHODS FOR COMPENSATING FOR A WORDLINE VOLTAGE IN-
CREASE

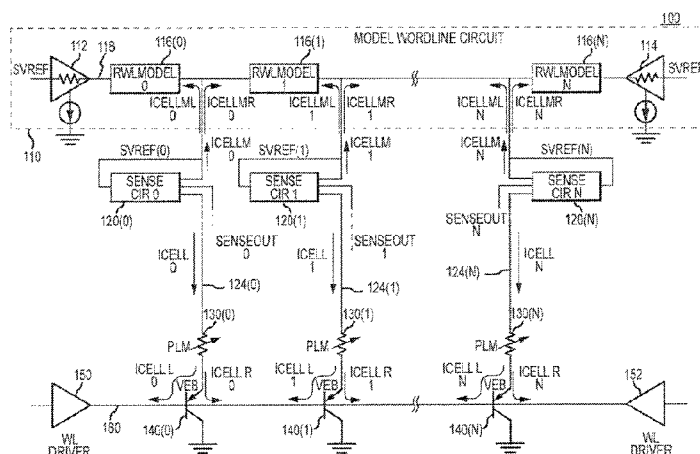


FIG. 1

- (57) **Abstract:** Apparatuses, sense circuits, and methods for compensating for a voltage increase on a wordline in a memory is de-
scribed. An example apparatus includes a bitline, a memory cell coupled to the bitline, a selector device coupled to the memory cell,
a wordline coupled to the selector device, and a wordline driver coupled to the wordline. The apparatus further includes a model
wordline circuit configured to model an impedance of the wordline and an impedance of the wordline driver, and a sense circuit
coupled to the bitline and to the model wordline circuit. The sense circuit is configured to sense a state of the memory cell based on
a cell current and provide a sense signal indicating a state of the memory cell. The sense circuit is further configured to adjust a
bitline voltage responsive to an increase in wordline voltage as modeled by the model wordline circuit.